

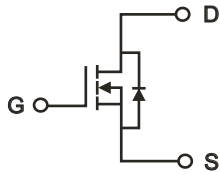
## 2N7002-HF (N-Channel) RoHS Device



### Features

- Halogen free.
- Power dissipation : 0.35W

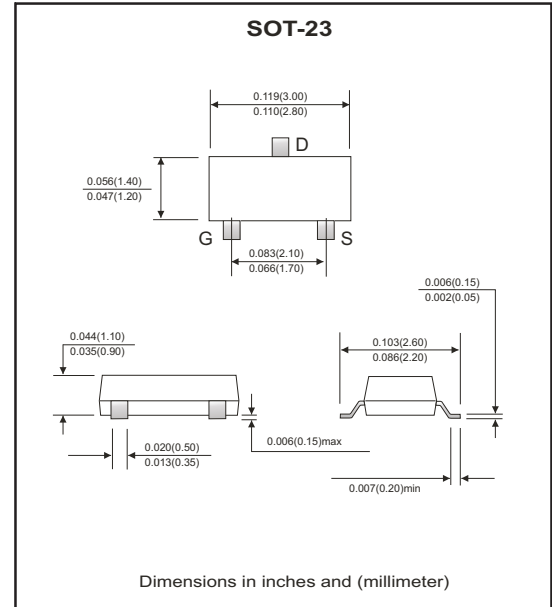
### Equivalent Circuit



G : Gate  
S : Source  
D : Drain

### Maximum Ratings (at TA=25°C)

Parameter	Symbol	Value	Unit
Drain-Source voltage	$V_{DS}$	60	V
Drain current	$I_D$	250	mA
Power dissipation	$P_D$	350	mW
Junction and storage temperature	$T_J, T_{STG}$	-55 ~ +150	°C



### Electrical Characteristics (at TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Drain-Source breakdown voltage	$V_{GS}=0V, I_D=10\mu A$	$V_{(BR)DS}$	60	70		V
Gate-Threshold voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	$V_{th(GS)}$	1	1.5	2.5	
Gate-body leakage	$V_{DS}=0V, V_{GS}=15V$	$I_{GSS}$			10	nA
Zero gate voltage drain current	$V_{DS}=60V, V_{GS}=0V$	$I_{DSS}$			1	$\mu A$
	$V_{DS}=60V, V_{GS}=0V, T_J=125^\circ C$				500	
On-state drain current	$V_{GS}=10V, V_{DS}=7.5V$	$I_{D(ON)}$	800	1300		mA
	$V_{GS}=4.5V, V_{DS}=10V$		500	700		
Drain-Source on resistance	$V_{GS}=10V, I_D=250mA$	$r_{DS(ON)}$		1.5	3	$\Omega$
	$V_{GS}=4.5V, I_D=200mA$			2.0	4	
Forward tran conductance	$V_{DS}=15V, I_D=200mA$	$g_{fs}$		300		mS
Diode forward voltage	$I_S=200mA, V_{GS}=0V$	$V_{SD}$		0.85	1.2	V
Total gate charge	$V_{DS}=30V, V_{GS}=10V, I_D=250mA$	$Q_g$		0.6	1.0	nC
Gate-Source charge		$Q_{gs}$		0.06		
Gate-Drain charge		$Q_{gd}$		0.06		
Input capacitance	$V_{DS}=25V, V_{GS}=0V, f=1MHz$	$C_{iss}$		25		pF
Output capacitance		$C_{oss}$		6		
Reverse transfer capacitance		$C_{rss}$		1.2		
Turn-on time	$V_{DD}=30V, R_L=200\Omega, I_D=100mA, V_{GEN}=10V, R_G=10\Omega$	$t_{d(ON)}$		7.5	20	nS
		$t_r$		6		
Turn-off time		$t_{d(off)}$		7.5	20	

## RATING AND CHARACTERISTIC CURVES (2N7002-HF)

Fig.1 On-Region Characteristics

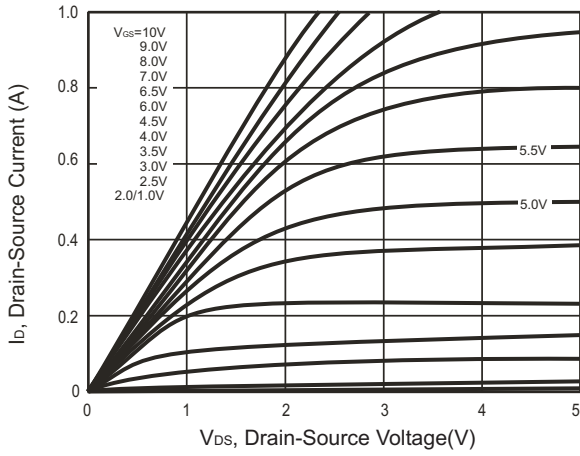


Fig.2 On-Resistance vs Drain Current

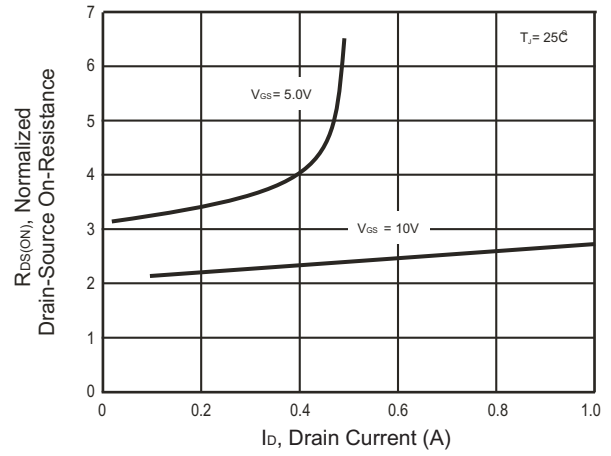


Fig.3 On-Resistance vs Junction Temperature

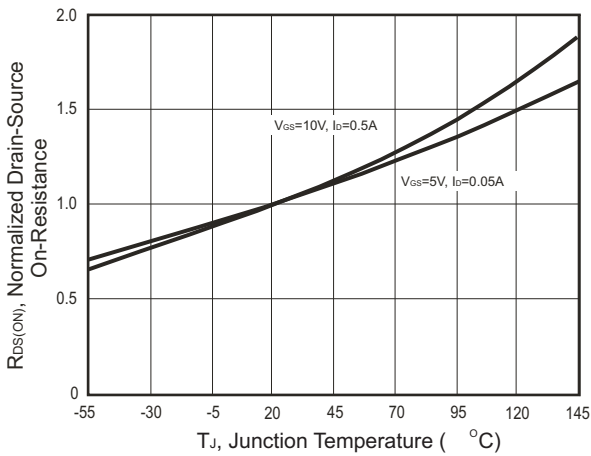


Fig.4 On-Resistance vs Gate-Source Voltage

